ABSTRACT OF THE DISCLOSURE

The present invention is intended to prevent the deterioration of resolution due to increase in off-axis aberration resulting from the deviation of a primary electron bean from the optical axis of a scanning electron microscope. A scanning electron microscope is provided with an image shifting deflector system including two deflectors disposed respectively at upper and lower stages. The deflector disposed at the lower stage is a multipole electrostatic deflecting electrode and is disposed in an objective. Even if the distance of image shifting is great, an image of a high resolution can be formed and dimensions can be measured in a high accuracy. The SEM is able to achieving precision inspection at a high throughput when applied to inspection in semiconductor device fabricating processes that process a wafer having a large area and provided with very minute circuit elements.